Title	Gate Control, Surface Leakage Currents and Peripheral Charging in AlGaN/GaN Heterostructure Field Effect Transistors Having Nanometer-Scale Schottky Gates
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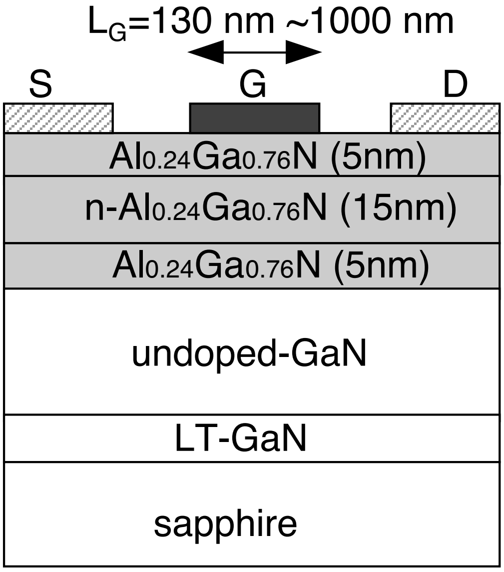
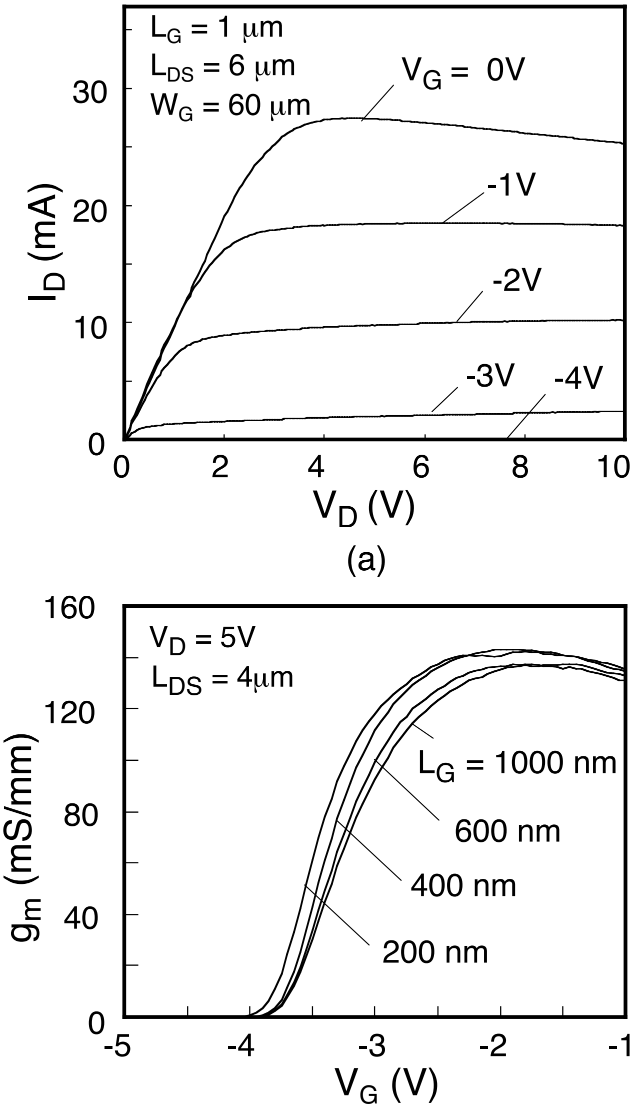


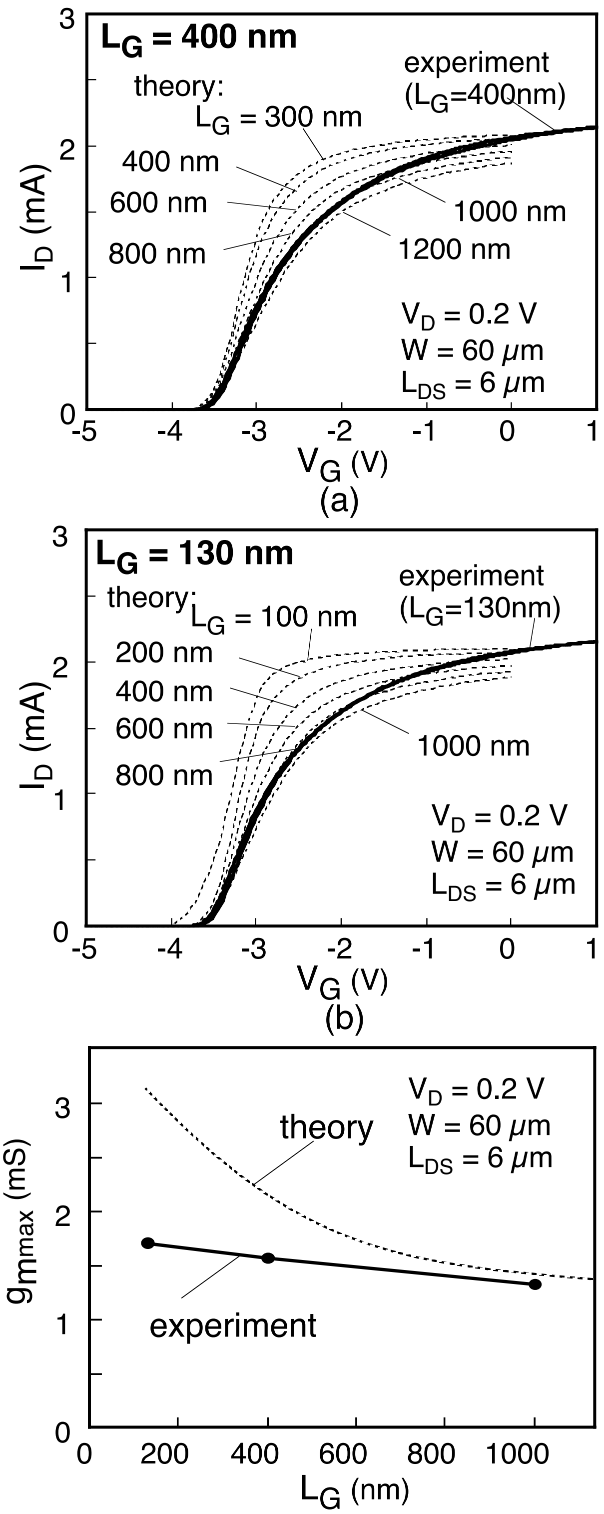
Figure 1, Kasai et al.



(a)

(b)

Figure 2, Kasai et al.

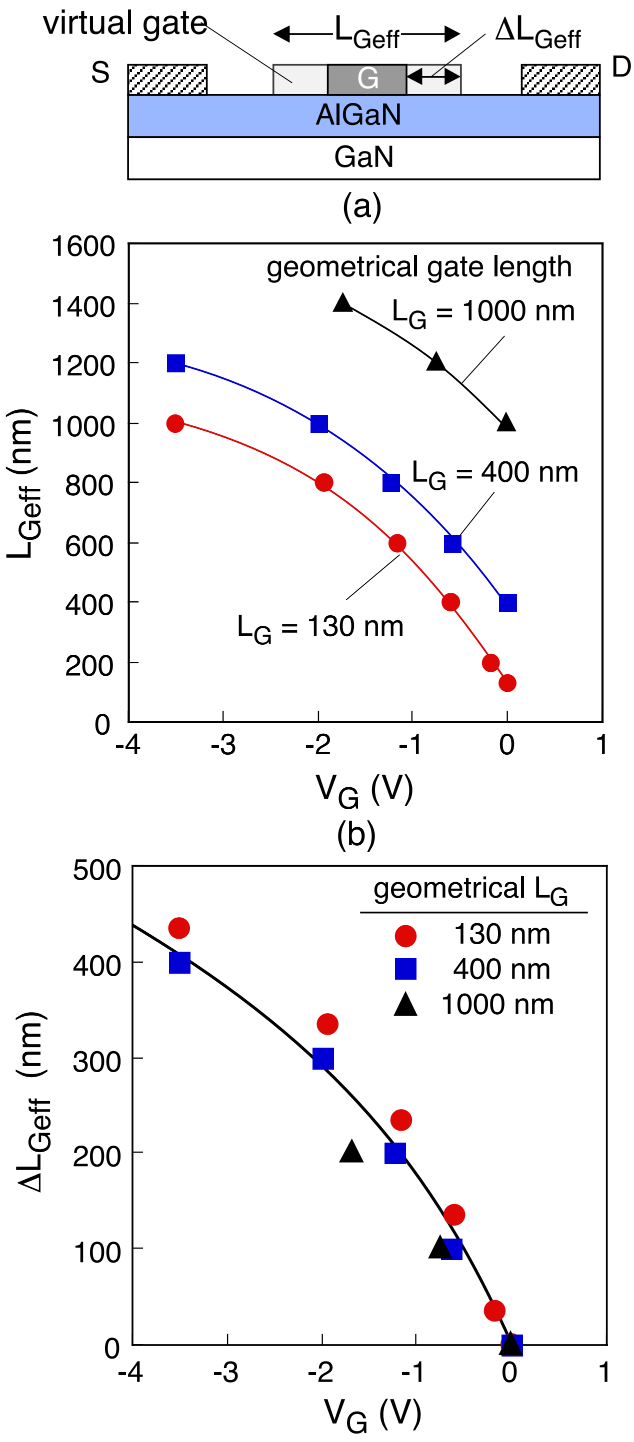


(a)

(b)

(c)

Figure 3, Kasai et al.



(a)

(b)

(c)

Figure 4, Kasai et al.

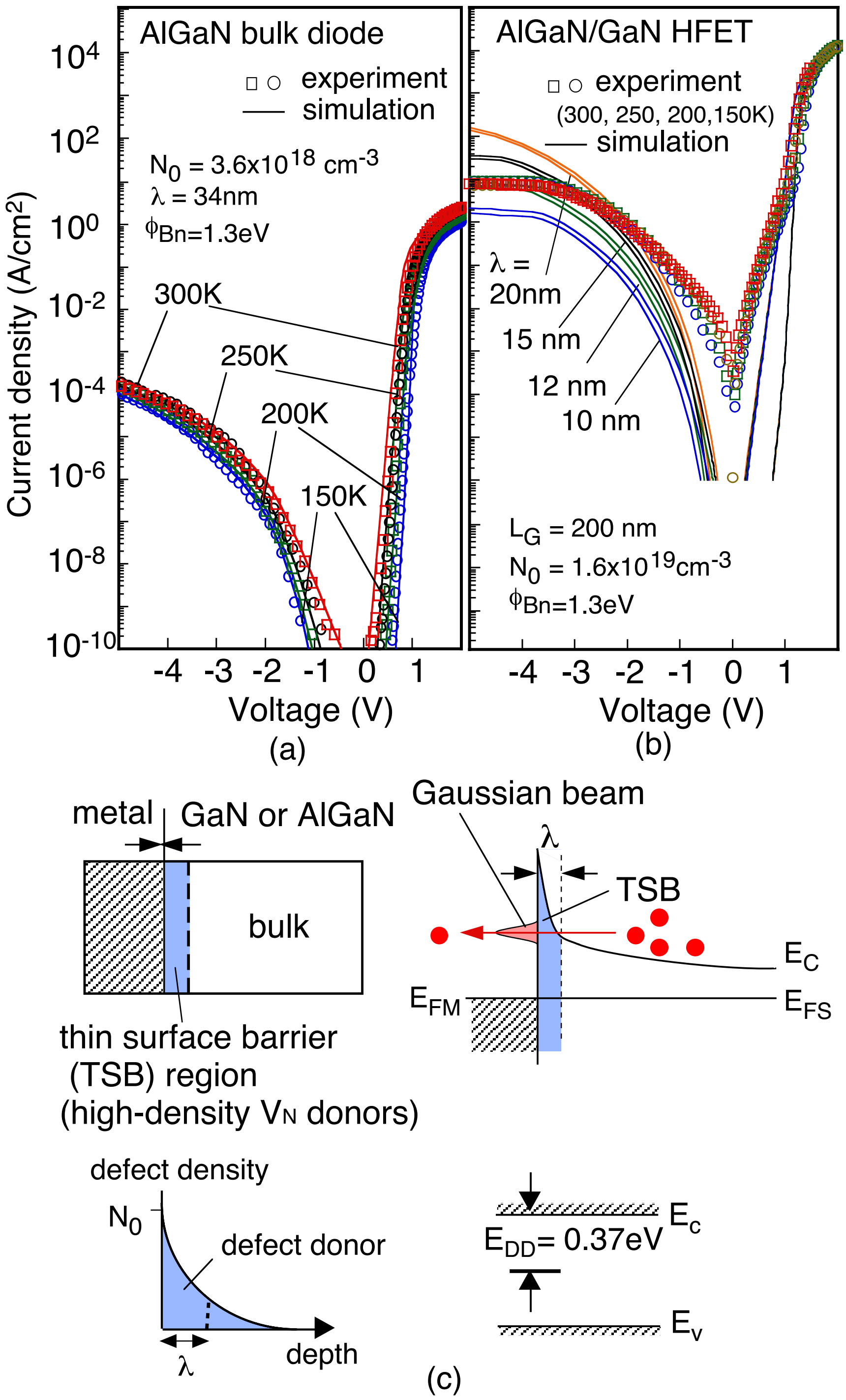


Figure 5, Kasai et al.

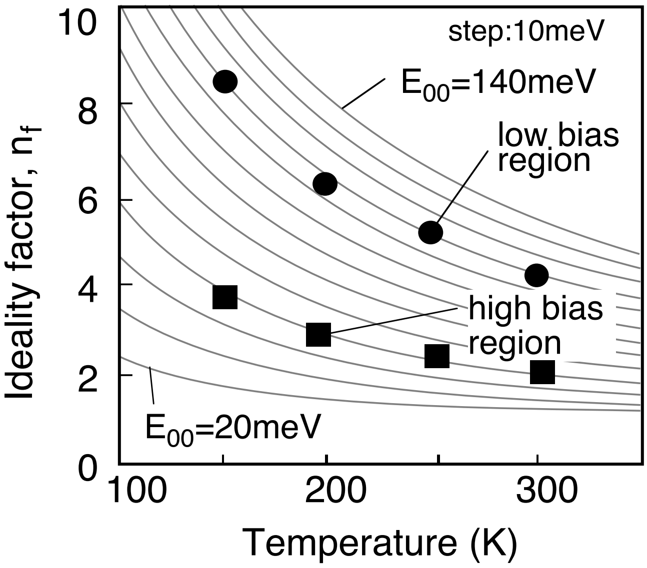
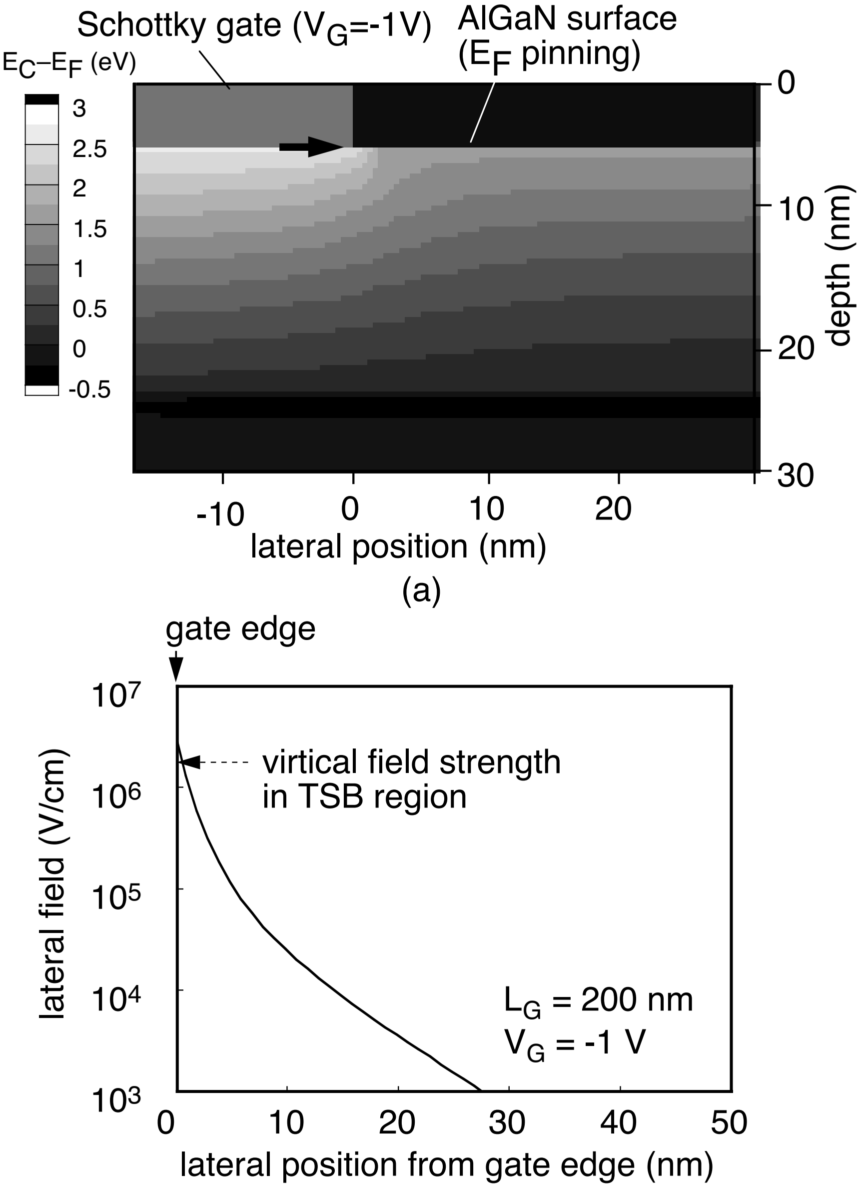


Figure 6, Kasai et al.



(a)

(b)

Figure 7, Kasai et al.

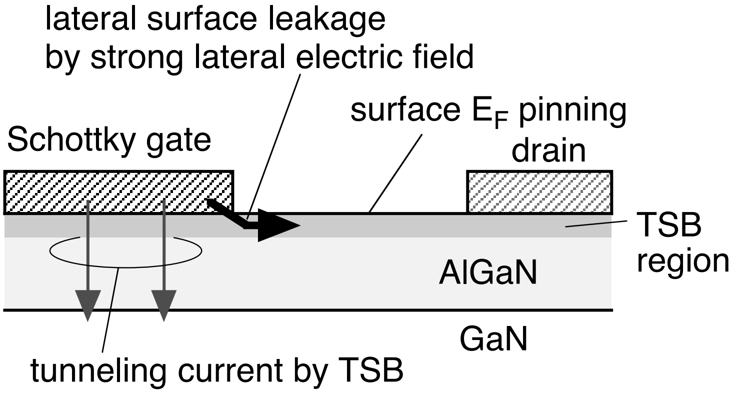


Figure 8, Kasai et al.

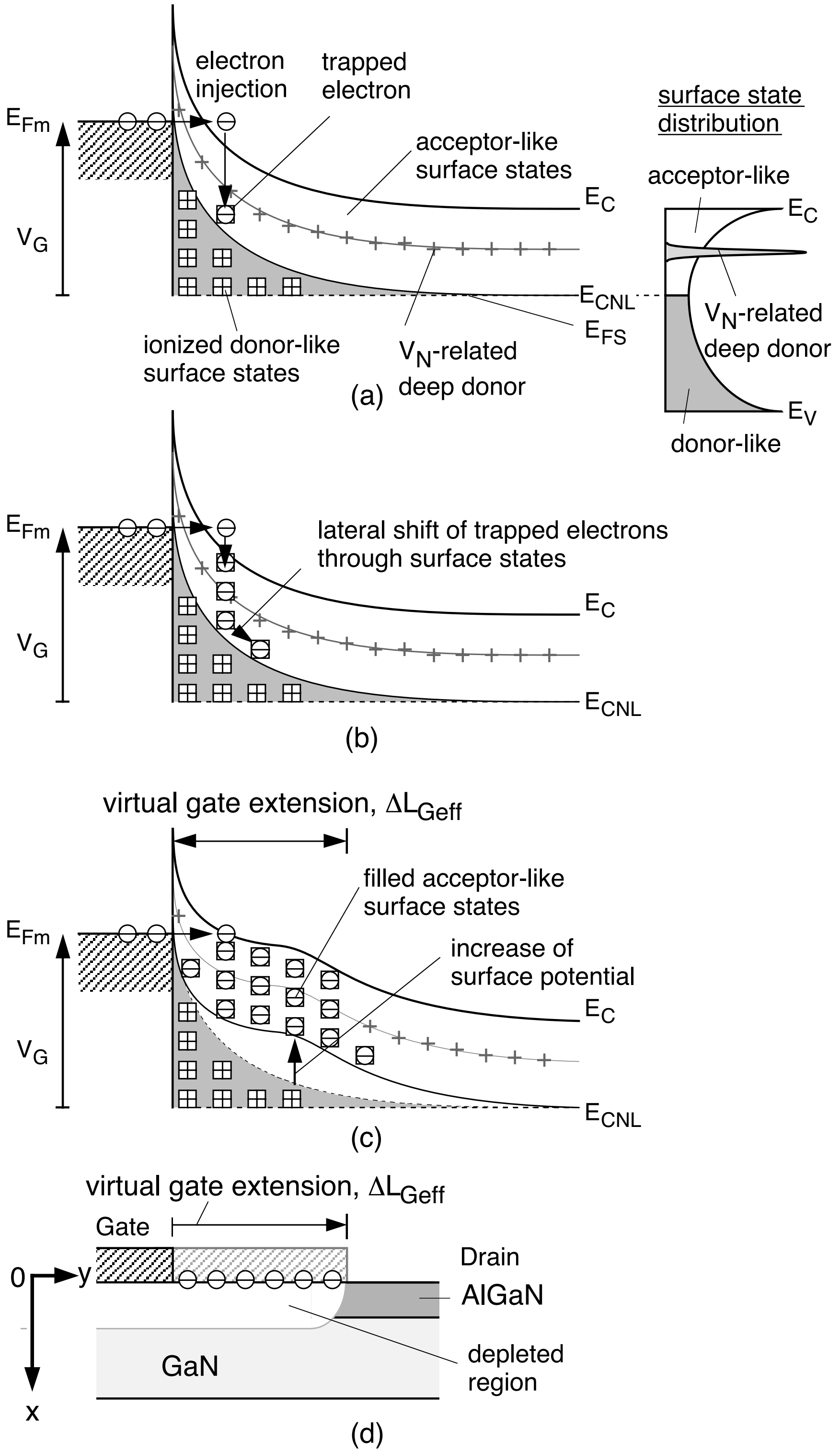


Figure 9, Kasai et al.